

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 3-5 have been amended and claims 7-11 have been added as follows:

Listing of Claims:

Claim 1 (original): A monocrystalline gallium nitride localized substrate comprising an area of grown monocrystalline gallium nitride locally on a monocrystalline silicon substrate.

Claim 2 (original): A monocrystalline gallium nitride localized substrate according to Claim 1, wherein said monocrystalline gallium nitride is grown on silicon carbide formed on the monocrystalline silicon substrate.

Claim 3 (currently amended): A monocrystalline gallium nitride localized substrate according to ~~any one of~~ Claim [[s]] 1 [[and 2]], wherein said monocrystalline gallium nitride is grown by using silicon nitride as a mask.

Claim 4 (currently amended): A monocrystalline gallium nitride localized substrate according to ~~any one of~~ Claim [[s]] 1 [[and 2]], wherein said monocrystalline gallium nitride is grown by using silicon oxide as a mask.

Claim 5 (currently amended): A monocrystalline gallium nitride localized substrate according to ~~any one of~~ Claim [[s]] 1 [[to 4]], wherein said monocrystalline silicon substrate is an SOI substrate.

Claim 6 (original): A method of manufacturing a monocrystalline gallium nitride localized substrate comprising the steps of:

forming silicon carbide on a monocrystalline silicon substrate; and
locally forming monocrystalline gallium nitride on said silicon carbide;
the method, wherein silicon nitride or silicon oxide is used as a mask in forming said monocrystalline gallium nitride.

Claim 7 (new): A monocrystalline gallium nitride localized substrate according to Claim 2, wherein said monocrystalline gallium nitride is grown by using silicon nitride as a mask.

Claim 8 (new): A monocrystalline gallium nitride localized substrate according to Claim 2, wherein said monocrystalline gallium nitride is grown by using silicon oxide as a mask.

Claim 9 (new): A monocrystalline gallium nitride localized substrate according to Claim 2, wherein said monocrystalline silicon substrate is an SOI substrate.

Claim 10 (new): A monocrystalline gallium nitride localized substrate according to Claim 3, wherein said monocrystalline silicon substrate is an SOI substrate.

Claim 11 (new): A monocrystalline gallium nitride localized substrate according to Claim 4, wherein said monocrystalline silicon substrate is an SOI substrate.